

ABSTRACT

5       An object of the present invention is to provide a gallium nitride compound semiconductor light-emitting device having a positive electrode that exhibits low contact resistance with a p-type gallium nitride compound semiconductor layer and that can be fabricated with high productivity.

10       The inventive gallium nitride compound semiconductor light-emitting device includes a substrate, an n-type semiconductor layer, a light-emitting layer, a p-type semiconductor layer, a negative electrode provided in contact with the n-type semiconductor layer, and a positive electrode provided in contact with the p-type semiconductor layer, the layers being successively provided atop the substrate in this order and being composed of a gallium nitride compound semiconductor, wherein

15       the positive electrode includes at least a contact metal layer which is in contact with the p-type semiconductor layer,

20       the contact metal layer comprises at least one metal selected from the group consisting of Pt, Ir, Rh, Pd, Ru, Re, and Os, or an alloy containing said at least one metal, and

25       the surface portion of the p-type semiconductor layer on the positive electrode side includes a positive-electrode-metal-containing layer that contains at least one metal selected from the group consisting of Pt, Ir, Rh, Pd, Ru, Re, and Os.